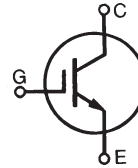


High Voltage IGBT

IXGH 32N170
IXGT 32N170

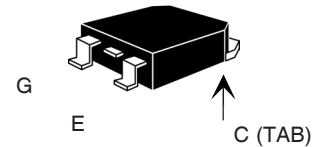
$V_{CES} = 1700 \text{ V}$
 $I_{C25} = 75 \text{ A}$
 $V_{CE(sat)} = 3.3 \text{ V}$
 $t_{fi(typ)} = 250 \text{ ns}$

Preliminary Data Sheet

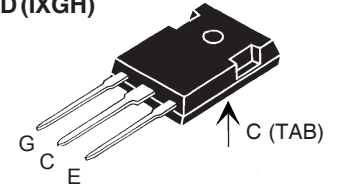


Symbol	Test Conditions	Maximum Ratings
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	1700 V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	1700 V
V_{GES}	Continuous	$\pm 20 \text{ V}$
V_{GEM}	Transient	$\pm 30 \text{ V}$
I_{C25}	$T_C = 25^\circ\text{C}$	75 A
I_{C90}	$T_C = 90^\circ\text{C}$	32 A
I_{CM}	$T_C = 25^\circ\text{C}, 1 \text{ ms}$	200 A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 5 \Omega$ Clamped inductive load	$I_{CM} = 90 \text{ A}$ @ $0.8 V_{CES}$
P_C	$T_C = 25^\circ\text{C}$	350 W
T_J		-55 ... +150 $^\circ\text{C}$
T_{JM}		150 $^\circ\text{C}$
T_{stg}		-55 ... +150 $^\circ\text{C}$
Maximum Lead temperature for soldering		300 $^\circ\text{C}$
1.6 mm (0.062 in.) from case for 10 s		
Maximum Tab temperature for soldering SMD devices for 10 s		260 $^\circ\text{C}$
M_d	Mounting torque (M3)	1.13/10Nm/lb.in.
Weight	TO-247 AD	6 g
	TO-268	4 g

TO-268 (IXGT)



TO-247 AD (IXGH)



G = Gate, E = Emitter, C = Collector, TAB = Collector

Features

- International standard packages JEDEC TO-268 and JEDEC TO-247 AD
- High current handling capability
- MOS Gate turn-on - drive simplicity
- Rugged NPT structure
- Molding epoxies meet UL 94 V-0 flammability classification

Applications

- Capacitor discharge & pulser circuits
- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies

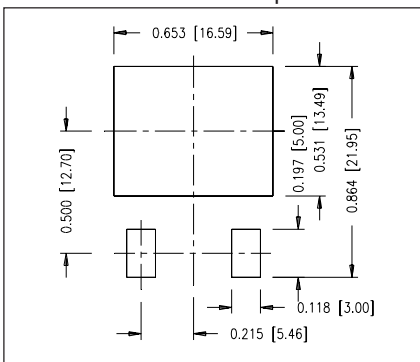
Advantages

- High power density
- Suitable for surface mounting
- Easy to mount with 1 screw, (isolated mounting screw hole)

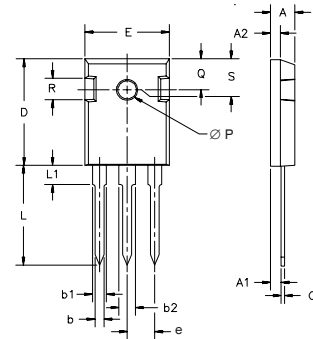
Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 250 \mu\text{A}, V_{GE} = 0 \text{ V}$	1700		V
$V_{GE(th)}$	$I_C = 250 \mu\text{A}, V_{CE} = V_{GE}$	3.0		V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 \text{ V}$			50 μA 1 mA
I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}, V_{GE} = 15 \text{ V}$		2.5 3.0	3.3 V V

Symbol	Test Conditions	Characteristic Values			
		(T _J = 25°C, unless otherwise specified)			
		min.	typ.	max.	
g_{fs}	I _C = I _{C90} ; V _{CE} = 10 V, Pulse test, t ≤ 300 μs, duty cycle ≤ 2 %	22	30	S	
I_{C(ON)}	V _{GE} = 10 V, V _{CE} = 10 V		120	A	
C_{ies}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		3500	pF	
C_{oes}		165	pF		
C_{res}		40	pF		
Q_g	I _C = I _{C90} , V _{GE} = 15 V, V _{CE} = 0.5 V _{CES}		155	nC	
Q_{ge}		30	nC		
Q_{gc}		51	nC		
t_{d(on)}	Inductive load, T_J = 25°C I _C = I _{C90} , V _{GE} = 15 V V _{CE} = 0.6 V _{CES} , R _G = R _{off} = 2.7 Ω		45	ns	
t_{ri}		38	ns		
t_{d(off)}		270	500	ns	
t_{fi}		250	500	ns	
E_{off}		11	20	mJ	
t_{d(on)}		Inductive load, T_J = 125°C I _C = I _{C90} , V _{GE} = 15 V V _{CE} = 0.6 V _{CES} , R _G = R _{off} = 2.7 Ω		48	ns
t_{ri}	42		ns		
E_{on}	6.0		mJ		
t_{d(off)}	360		ns		
t_{fi}	560		ns		
E_{off}	14		mJ		
R_{thJC}				0.35	K/W
R_{thCK}	(TO-247)	0.25			K/W

Min Recommended Footprint

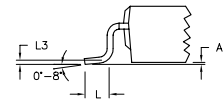
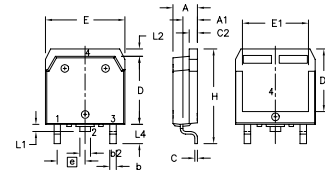


TO-247 AD Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L1		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

TO-268 Outline



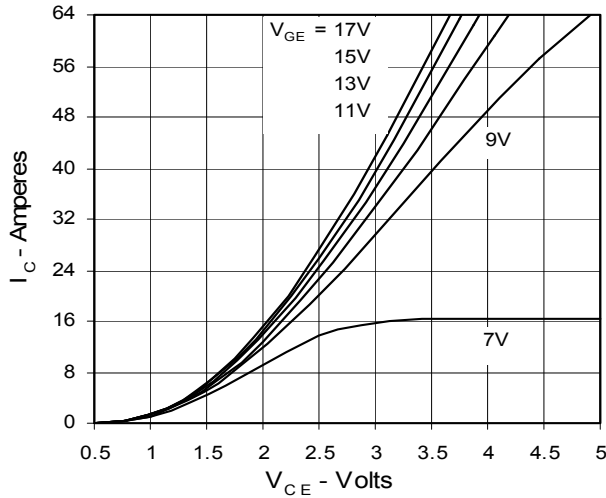
Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.9	5.1	.193	.201
A ₁	2.7	2.9	.106	.114
A ₂	.02	.25	.001	.010
b	1.15	1.45	.045	.057
b ₂	1.9	2.1	.75	.83
C	.4	.65	.016	.026
D	13.80	14.00	.543	.551
E	15.85	16.05	.624	.632
E ₁	13.3	13.6	.524	.535
e	5.45	BSC	.215	BSC
H	18.70	19.10	.736	.752
L	2.40	2.70	.094	.106
L1	1.20	1.40	.047	.055
L2	1.00	1.15	.039	.045
L3		0.25 BSC		.010 BSC
L4	3.80	4.10	.150	.161

IXYS reserves the right to change limits, test conditions, and dimensions.

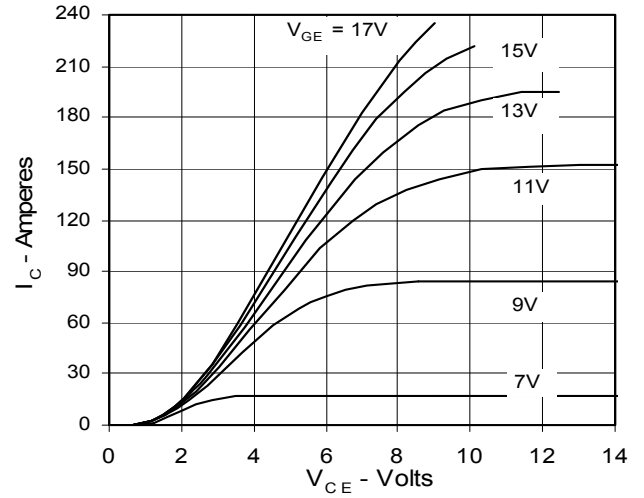
IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:

4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1 6,259,123B1 6,306,728B1
4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025 6,404,065B1 6,162,665 6,534,343 6,583,505

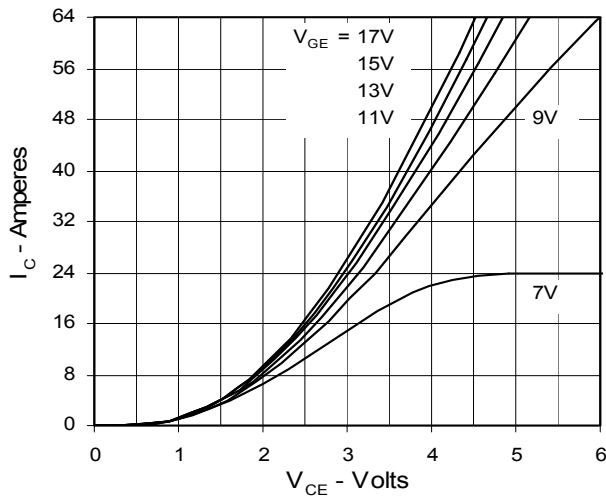
**Fig. 1. Output Characteristics
@ 25 Deg. C**



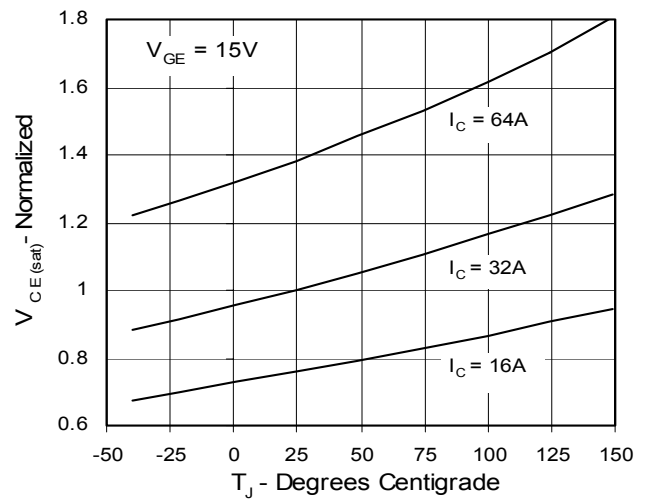
**Fig. 2. Extended Output Characteristics
@ 25 deg. C**



**Fig. 3. Output Characteristics
@ 125 Deg. C**



**Fig. 4. Dependence of $V_{CE(sat)}$ on
Temperature**



**Fig. 5. Collector-to-Emitter Voltage
vs. Gate-to-Emitter voltage**

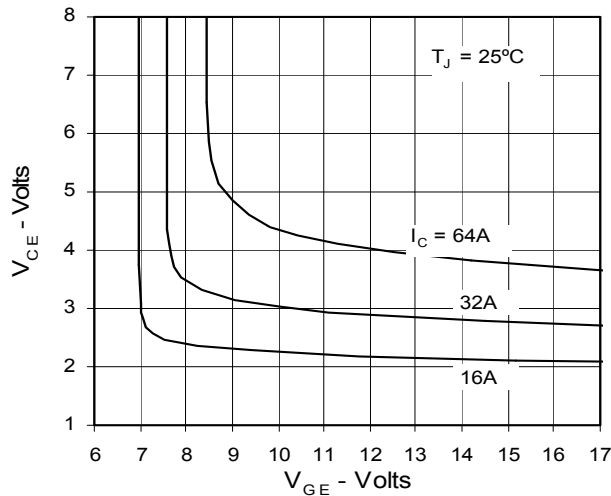


Fig. 6. Input Admittance

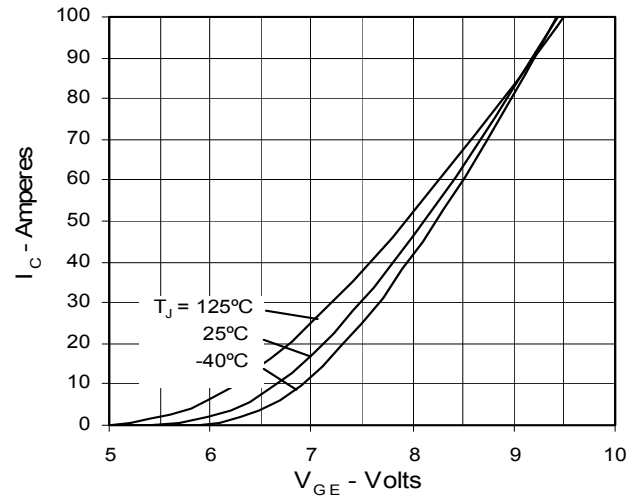


Fig. 7. Transconductance

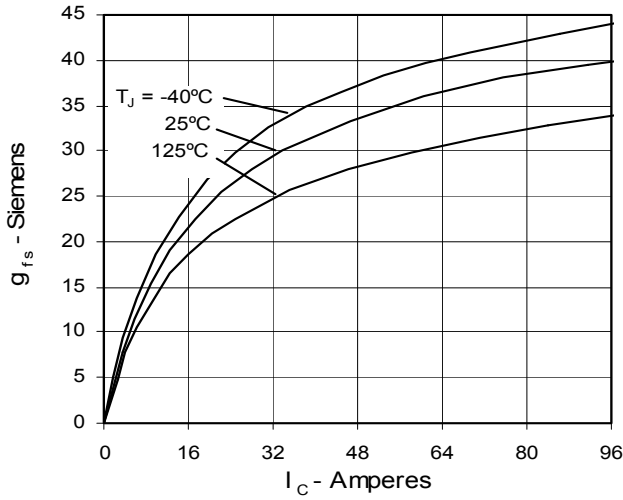


Fig. 8. Dependence of E_{off} on R_G

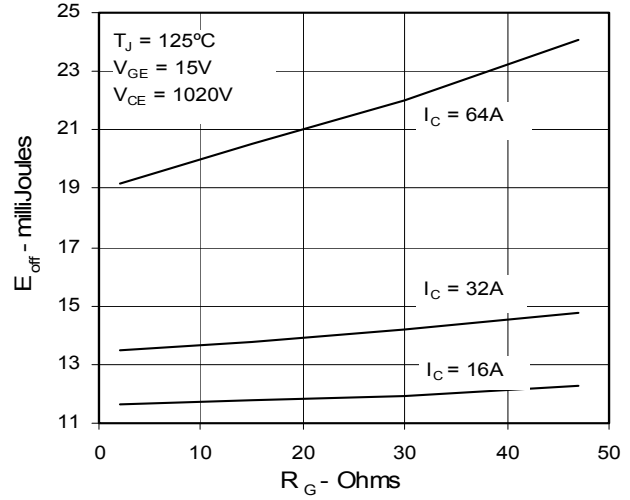


Fig. 9. Dependence of E_{off} on I_c

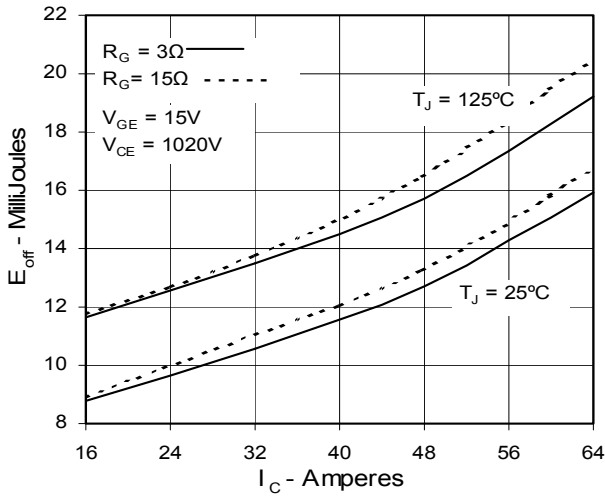


Fig. 10. Dependence of E_{off} on Temperature

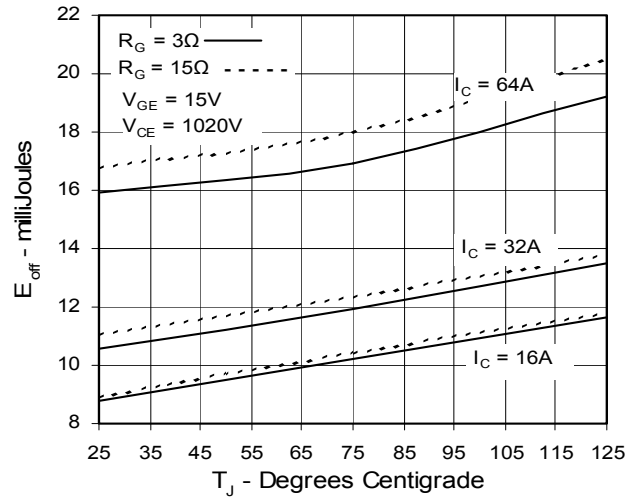


Fig. 11. Gate Charge

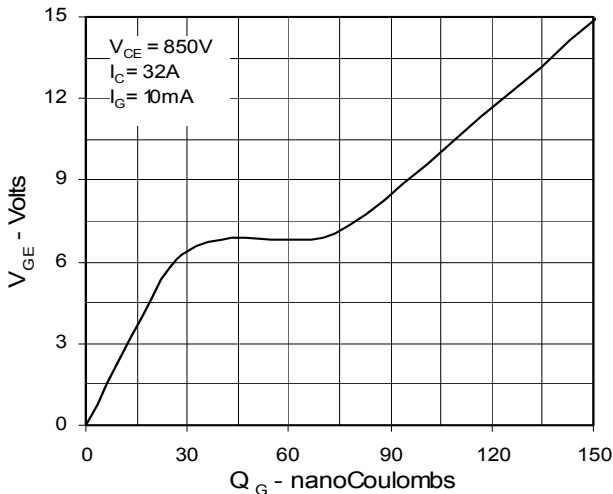
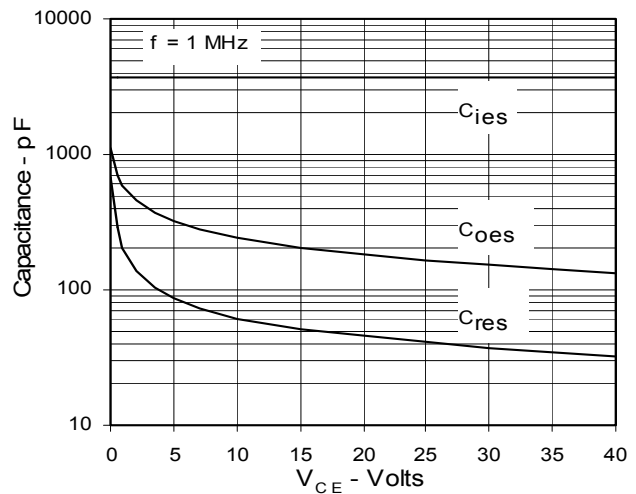


Fig. 12. Capacitance



IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: 4,835,592 4,881,106 5,017,508 5,049,961 5,187,117 5,486,715 6,306,728B1 6,259,123B1 6,306,728B1 4,850,072 4,931,844 5,034,796 5,063,307 5,237,481 5,381,025 6,404,065B1 6,162,665 6,534,343 6,583,505

Fig. 13. Maximum Transient Thermal Resistance

